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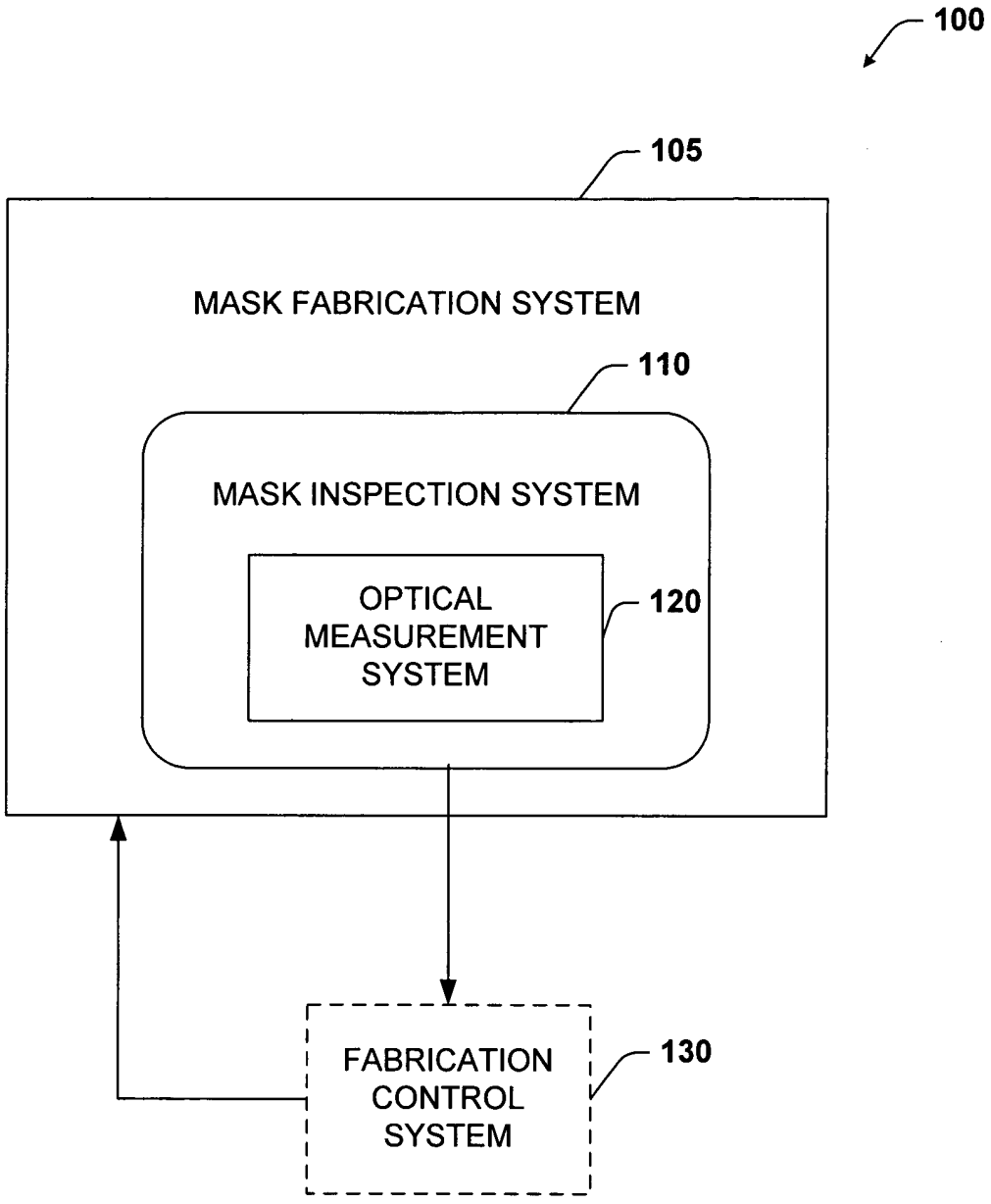

FIG. 1

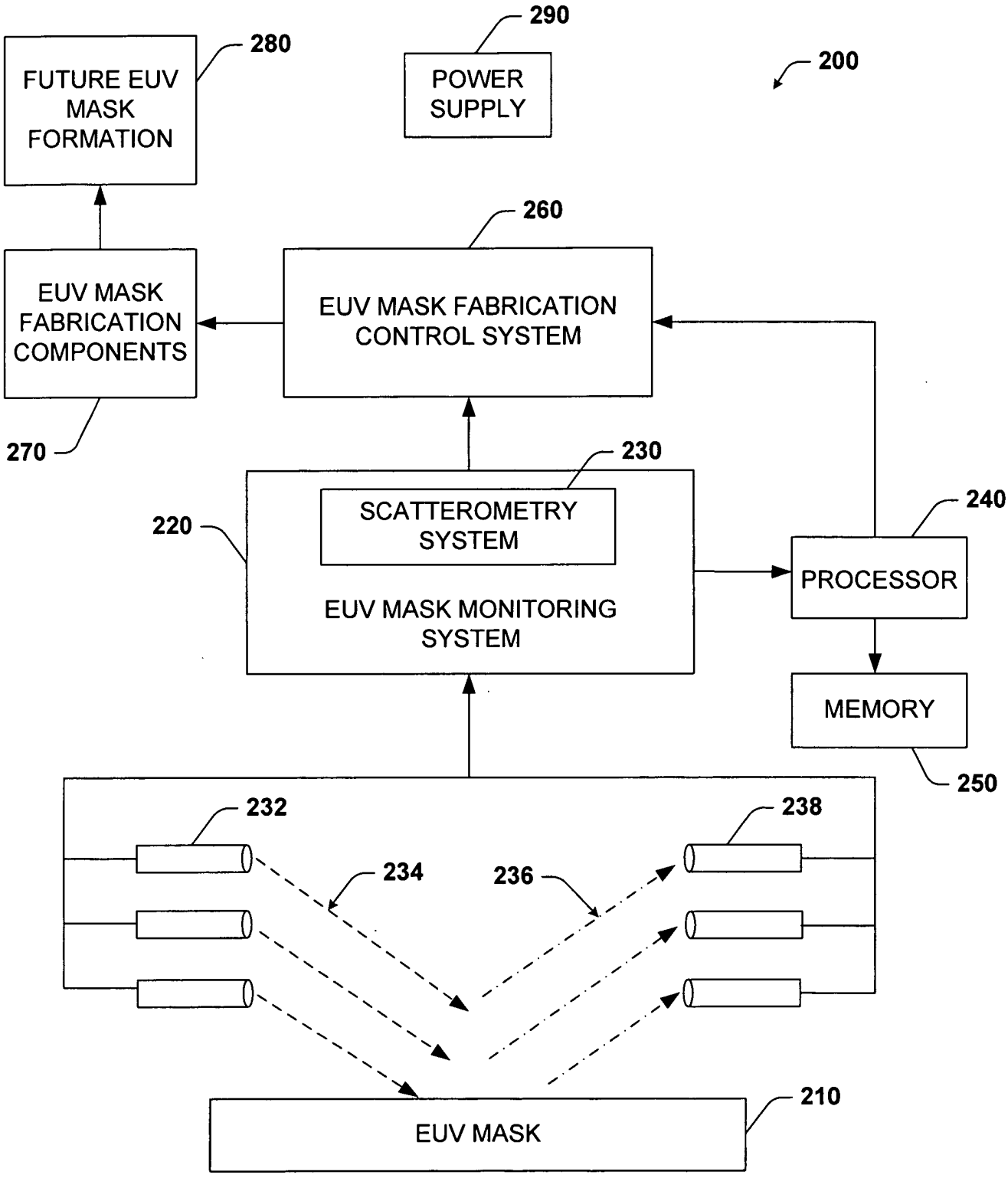
290
280
FUTURE EUV MASK FORMATION
POWER SUPPLY
200
260
EUV MASK FABRICATION CONTROL SYSTEM
EUV MASK FABRICATION COMPONENTS
270
230
220
SCATTEROMETRY SYSTEM
EUV MASK MONITORING SYSTEM
240
PROCESSOR
MEMORY
250
232
238
234
236
210
EUV MASK

FIG. 2

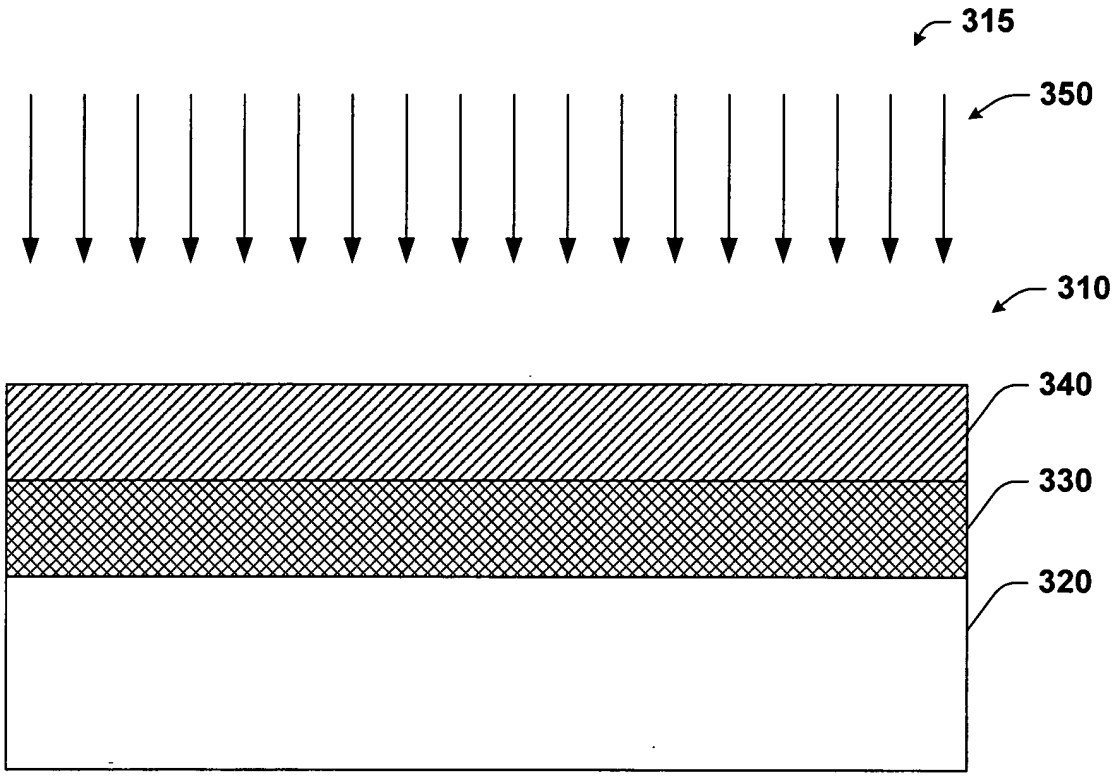

FIG. 3

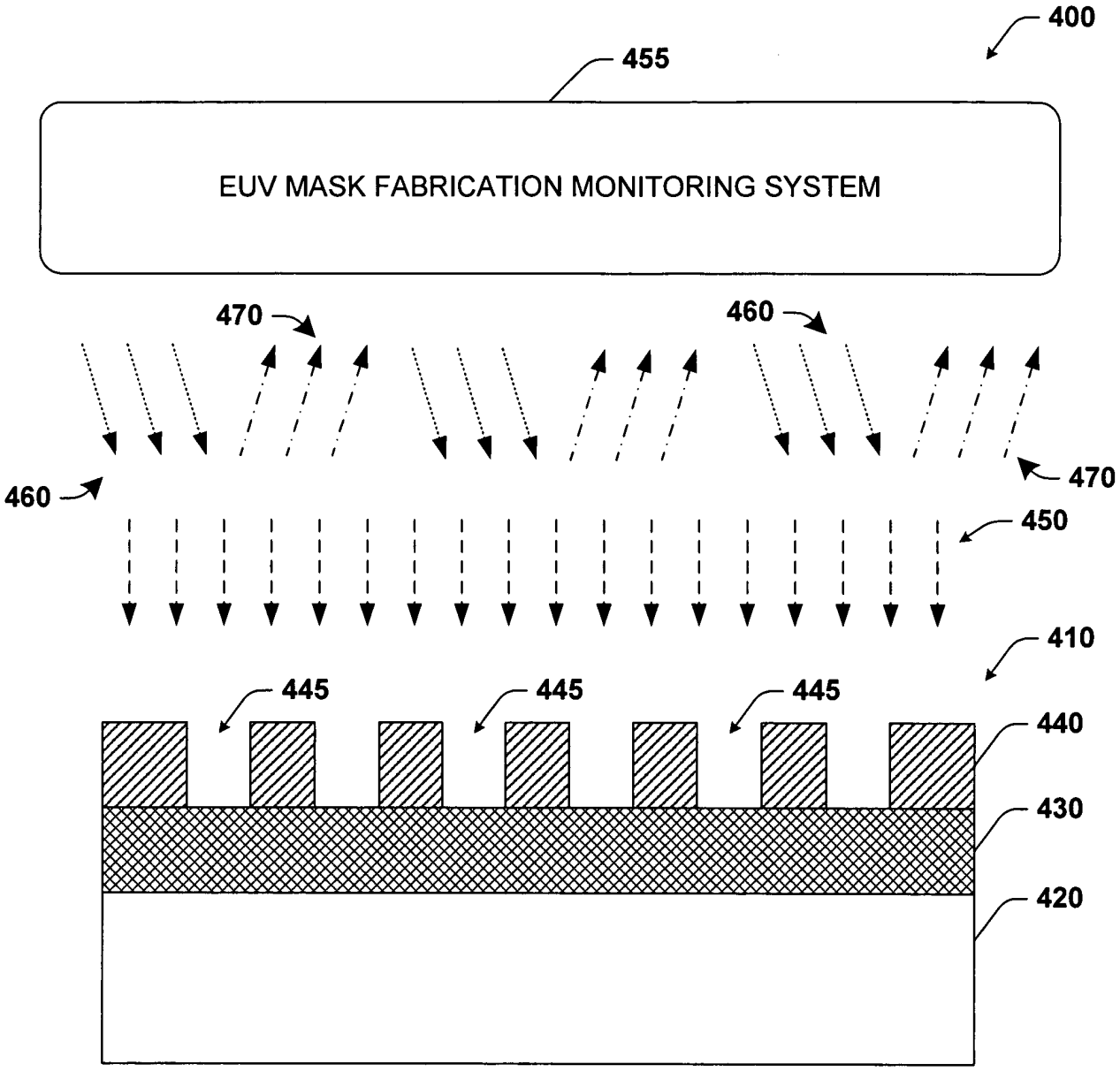
400
455
EUV MASK FABRICATION MONITORING SYSTEM
470
460
460
470
450
410
445
445
445
440
430
420

FIG. 4

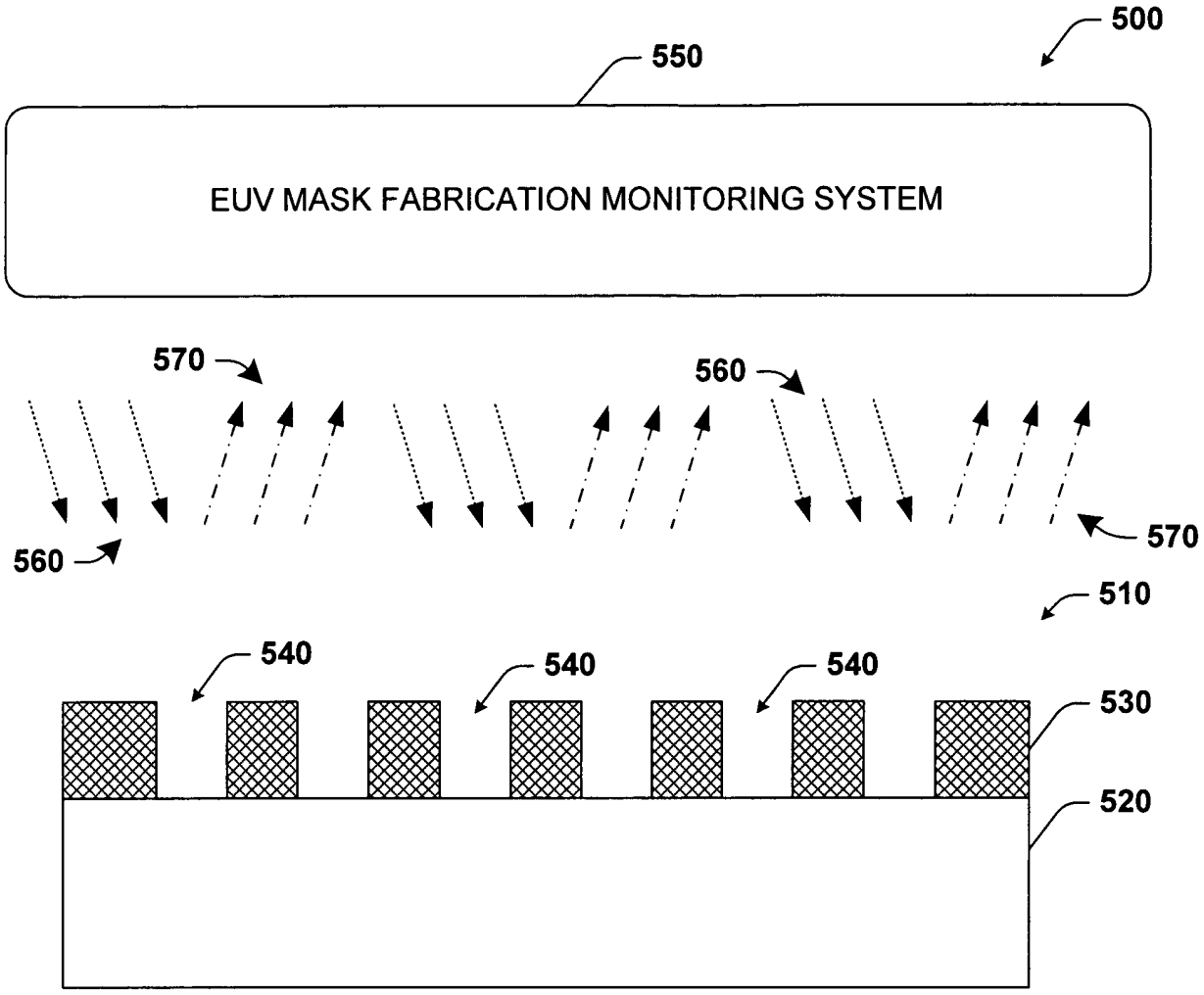
500
550
EUV MASK FABRICATION MONITORING SYSTEM
570
560
560
570
510
540
540
540
530
520

FIG. 5

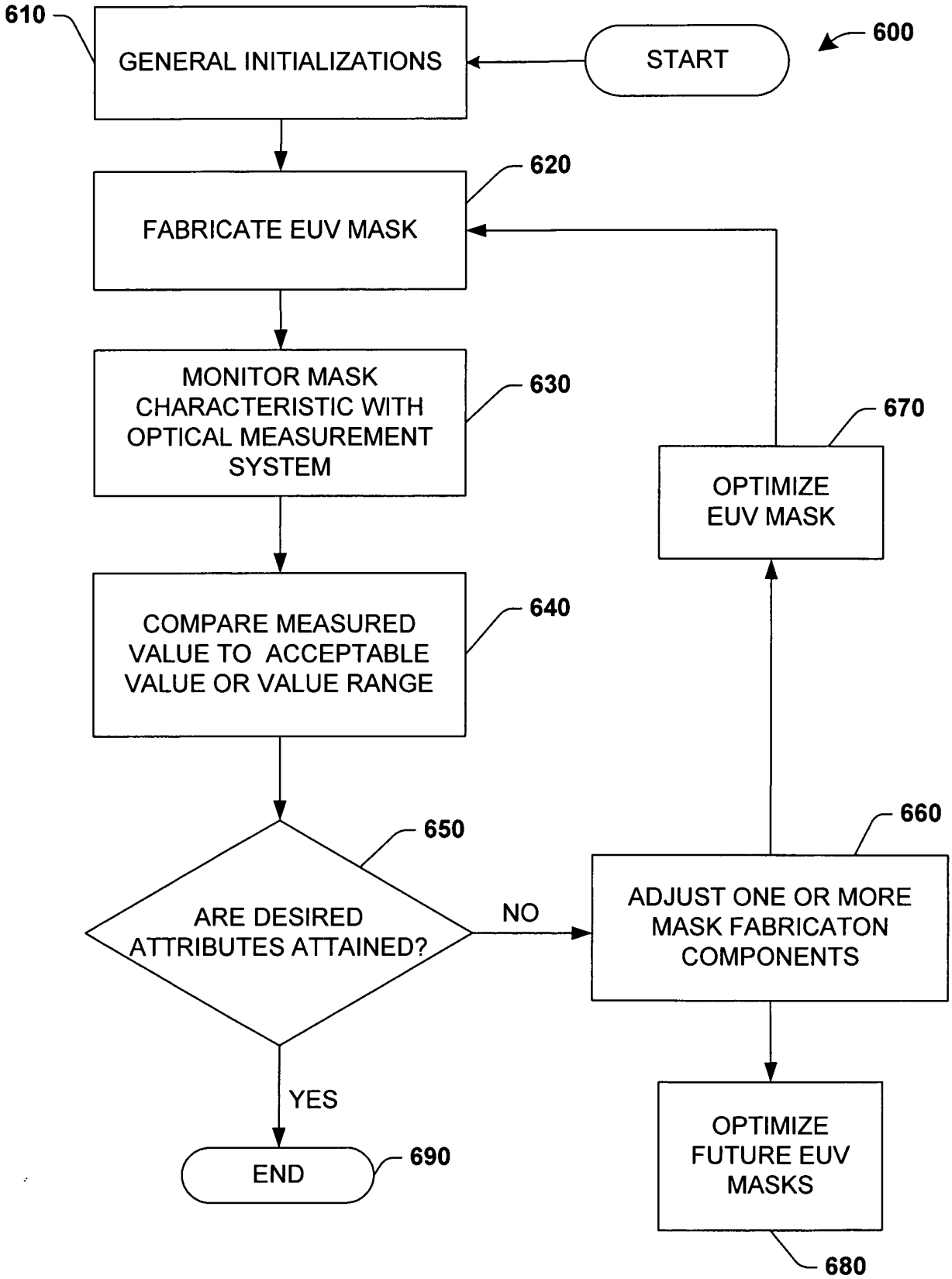
610
GENERAL INITIALIZATIONS
START
600
620
FABRICATE EUV MASK
MONITOR MASK CHARACTERISTIC WITH OPTICAL MEASUREMENT SYSTEM
630
670
OPTIMIZE EUV MASK
COMPARE MEASURED VALUE TO ACCEPTABLE VALUE OR VALUE RANGE
640
650
ARE DESIRED ATTRIBUTES ATTAINED?
NO
660
ADJUST ONE OR MORE MASK FABRICATON COMPONENTS
YES
END
690
OPTIMIZE FUTURE EUV MASKS
680

FIG. 6